

# **BUK7S0R5-40H**

# N-channel 40 V, 0.5 mOhm standard level MOSFET in LFPAK88

6 April 2021

**Product data sheet** 

### 1. General description

Automotive qualified N-channel MOSFET using the latest Trench 9 low ohmic superjunction technology, housed in a copper-clip LFPAK88 package. This product has been fully designed and qualified to meet beyond AEC-Q101 requirements delivering high performance and reliability.

### 2. Features and benefits

- · Fully automotive qualified to beyond AEC-Q101:
  - -55 °C to +175 °C rating suitable for thermally demanding environments
- LFPAK88 package
  - Designed for smaller footprint and improved power density over older wire bond packages such as D<sup>2</sup>PAK for today's space constrained high power automotive applications
  - Thin package and copper clip enables LFPAK88 to be highly efficient thermally
- LFPAK copper clip technology enabling improvements over wire bond packages by:
  - Increased maximum current capability and excellent current spreading
  - Improved R<sub>DSon</sub>
  - · Low source inductance
  - Low thermal resistance R<sub>th</sub>
- LFPAK Gull Wing leads:
  - Flexible leads enabling high Board Level Reliability absorbing mechanical and thermal cycling stress, unlike traditional QFN packages
  - Visual (AOI) soldering inspection, no need for expensive x-ray equipment
  - Easy solder wetting for good mechanical solder joint
- Unique 40 V Trench 9 superjunction technology:
  - Reduced cell pitch and superjunction platform enables lower R<sub>DSon</sub> in the same footprint
  - Improved SOA and avalanche capability compared to standard TrenchMOS
  - Tight V<sub>GS(th)</sub> limits enable easy paralleling of MOSFETs

# 3. Applications

- 12 V automotive systems
- 48 V DC/DC systems (on 12 V secondary side)
- Higher power motors, lamps and solenoid control
- Reverse polarity protection
- Ultra high performance power switching

### 4. Quick reference data

### Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
$V_{DS}$	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	-	40	V	
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	[1]	-	-	500	Α	
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	-	375	W	



Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static chara	acteristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 25 °C; Fig. 11		0.33	0.47	0.55	mΩ
Dynamic cl	haracteristics						
$Q_{GD}$	gate-drain charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 32 V; V <sub>GS</sub> = 10 V; Fig. 13; Fig. 14		-	32	65	nC
Source-dra	in diode						
Q <sub>r</sub>	recovered charge	$I_S = 25 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V}; V_{DS} = 20 \text{ V}; T_j = 25 °C$	[2]	-	93	-	nC
S	softness factor			-	0.83	-	

<sup>[1] 500</sup>A continuous current has been successfully demonstrated during application. Practically the current will be limited by PCB, thermal design and operating temperature.

### 5. Pinning information

### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		D
2	S	source		
3	S	source		G—(F)
4	S	source		mbb076 S
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK88 (SOT1235)	

# 6. Ordering information

#### **Table 3. Ordering information**

Type number	Package					
	Name	Description	Version			
BUK7S0R5-40H		plastic, single-ended surface-mounted package (LFPAK88); 4 leads; 2 mm pitch; 8 mm x 8 mm x 1.6 mm body	SOT1235			

### 7. Marking

#### Table 4. Marking codes

Type number	Marking code
BUK7S0R5-40H	7SOR540H

# 8. Limiting values

### **Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C	-	40	V

<sup>[2]</sup> includes capacitive recovery

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>GS</sub>	gate-source voltage	DC; T <sub>j</sub> = 175 °C		-10	20	V
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	375	W
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	[1]	-	500	Α
I <sub>DM</sub>	peak drain current	pulsed; t <sub>p</sub> ≤ 10 μs; T <sub>mb</sub> = 25 °C; <u>Fig. 3</u>		-	2237	Α
T <sub>stg</sub>	storage temperature			-55	175	°C
T <sub>j</sub>	junction temperature			-55	175	°C
Source-drain d	liode					
Is	source current	T <sub>mb</sub> = 25 °C	[1]	-	500	Α
I <sub>SM</sub>	peak source current	pulsed; t <sub>p</sub> ≤ 10 μs; T <sub>mb</sub> = 25 °C		-	2237	Α
Avalanche rug	gedness					
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$I_D$ = 120 A; $V_{sup} \le 40$ V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 4	[2] [3]	-	1375	mJ
I <sub>AS</sub>	non-repetitive avalanche current	$V_{sup} = 40 \text{ V}; V_{GS} = 10 \text{ V}; T_{j(init)} = 25 \text{ °C}; R_{GS} = 50 \Omega; Fig. 4$	[4]	-	315	A

- [1] 500A continuous current has been successfully demonstrated during application. Practically the current will be limited by PCB, thermal design and operating temperature.
- [2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
- [3] Refer to application note AN10273 for further information.
- [4] Protected by 100% test.

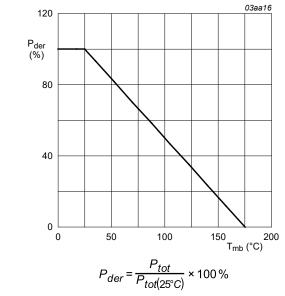
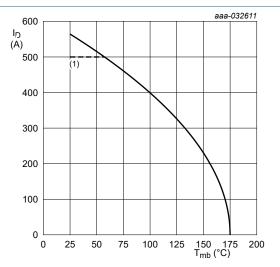


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

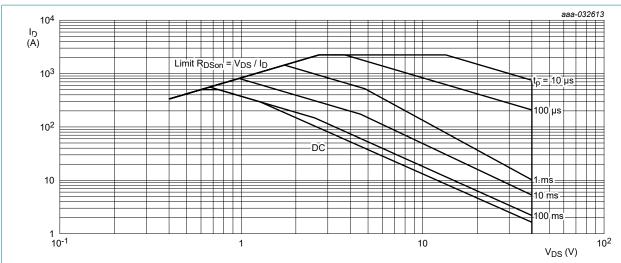


 $V_{GS} \ge 10 \text{ V}$ 

(1) 500A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

Fig. 2. Continuous drain current as a function of mounting base temperature

### N-channel 40 V, 0.5 mOhm standard level MOSFET in LFPAK88



 $T_{mb}$  = 25 °C;  $I_{DM}$  is a single pulse

Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

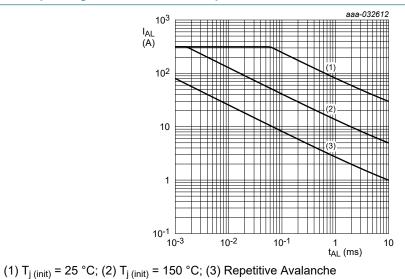


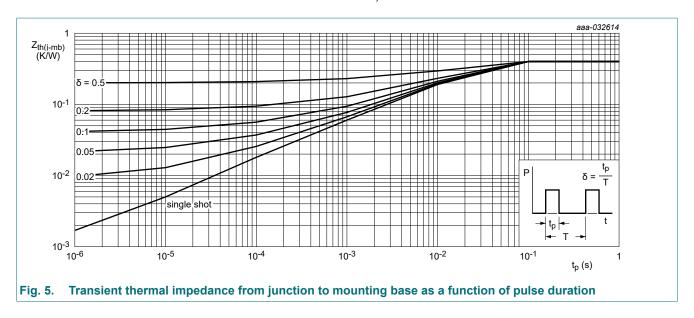
Fig. 4. Avalanche rating; avalanche current as a function of avalanche time

### 9. Thermal characteristics

#### **Table 6. Thermal characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	<u>Fig. 5</u>	-	0.35	0.4	K/W

### N-channel 40 V, 0.5 mOhm standard level MOSFET in LFPAK88



### 10. Characteristics

**Table 7. Characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics				_	
V <sub>(BR)DSS</sub>	drain-source	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	40	43	-	V
	breakdown voltage	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = -40 °C	-	40.5	-	V
		I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = -55 °C	36	40	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = 25 \text{ °C}; Fig. 9;$ Fig. 10	2.4	3	3.6	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}; Fig. 10$	-	-	4.3	V
		$I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = 175 \text{ °C};$ Fig. 10	1	-	-	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.2	2.9	μA
		V <sub>DS</sub> = 16 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 125 °C	-	4.6	25	μA
		V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C	-	455	1000	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
		V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 11	0.33	0.47	0.55	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 105 °C; Fig. 12	0.47	0.68	0.87	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 125 °C; Fig. 12	0.52	0.75	0.95	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C; Fig. 12	0.65	0.93	1.19	mΩ
R <sub>G</sub>	gate resistance	f = 1 MHz; T <sub>j</sub> = 25 °C	0.37	0.92	2.31	Ω
Dynamic ch	naracteristics		'			
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 32 V; V <sub>GS</sub> = 10 V;	-	190	267	nC
Q <sub>GS</sub>	gate-source charge	Fig. 13; Fig. 14	-	51	77	nC
Q <sub>GD</sub>	gate-drain charge		-	32	65	nC

### N-channel 40 V, 0.5 mOhm standard level MOSFET in LFPAK88

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 25 V; V <sub>GS</sub> = 0 V; f = 1 MHz;		-	15116	21162	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 15</u>		-	2718	3805	pF
C <sub>rss</sub>	reverse transfer capacitance			-	544	1197	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 30 \text{ V}; R_{L} = 1.2 \Omega; V_{GS} = 10 \text{ V};$ $R_{G(ext)} = 5 \Omega$		-	40	-	ns
t <sub>r</sub>	rise time			-	33	-	ns
t <sub>d(off)</sub>	turn-off delay time			-	117	-	ns
t <sub>f</sub>	fall time	_		-	48	-	ns
Source-dra	ain diode		'				
V <sub>SD</sub>	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}; Fig. 16$		-	0.79	1	V
t <sub>rr</sub>	reverse recovery time	$I_S = 25 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$		-	62	-	ns
Q <sub>r</sub>	recovered charge	$V_{DS} = 20 \text{ V}; T_j = 25 \text{ °C}$	[1]	-	93	-	nC
S	softness factor	1		-	0.83	-	
		$I_S$ = 25 A; $dI_S/dt$ = -500 A/ $\mu$ s; $V_{GS}$ = 0 V; $V_{DS}$ = 20 V; $T_j$ = 25 °C		-	0.73	-	

### [1] includes capacitive recovery

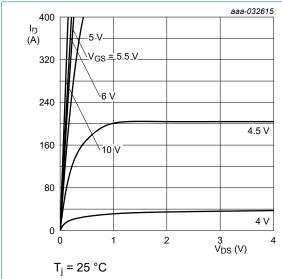


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

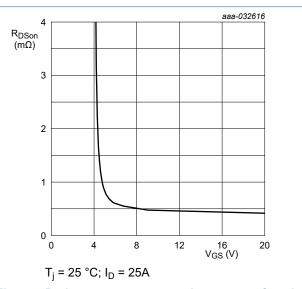


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

### N-channel 40 V, 0.5 mOhm standard level MOSFET in LFPAK88

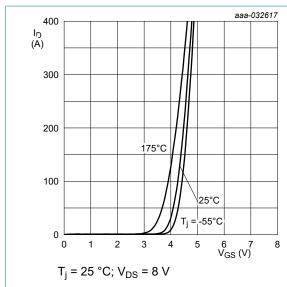


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values

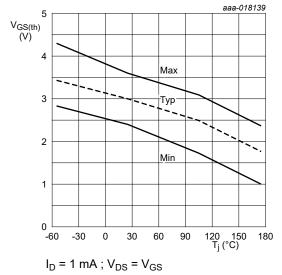


Fig. 10. Gate-source threshold voltage as a function of junction temperature

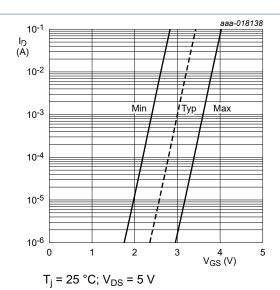


Fig. 9. Sub-threshold drain current as a function of gate-source voltage

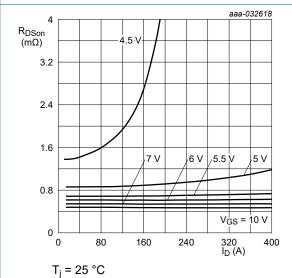


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

### N-channel 40 V, 0.5 mOhm standard level MOSFET in LFPAK88

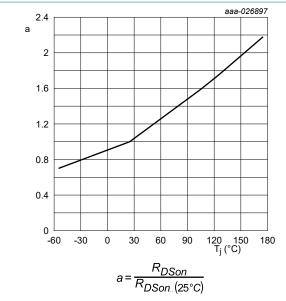


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

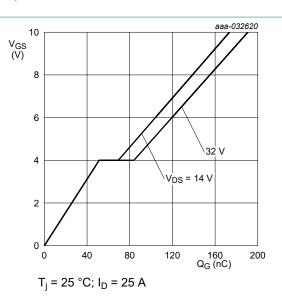


Fig. 13. Gate-source voltage as a function of gate charge; typical values

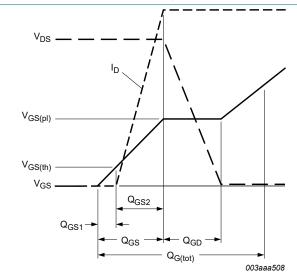
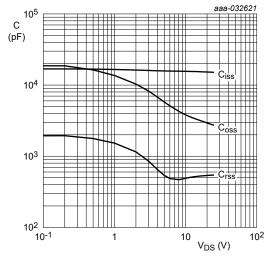


Fig. 14. Gate charge waveform definitions



 $V_{GS} = 0 V$ ; f = 1 MHz

Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

### N-channel 40 V, 0.5 mOhm standard level MOSFET in LFPAK88

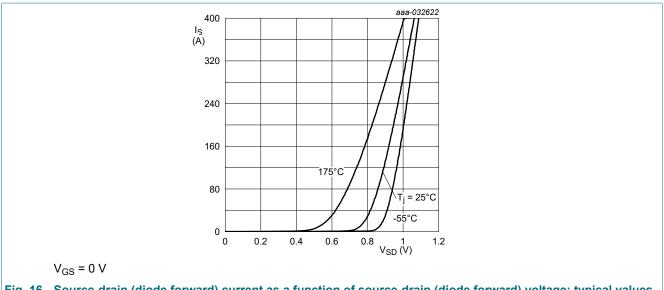


Fig. 16. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values

# 11. Package outline

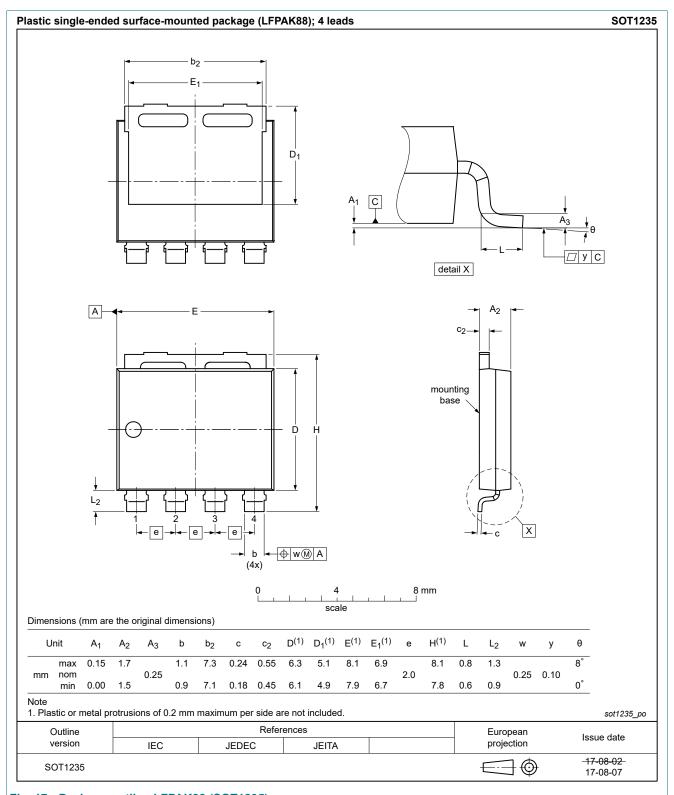
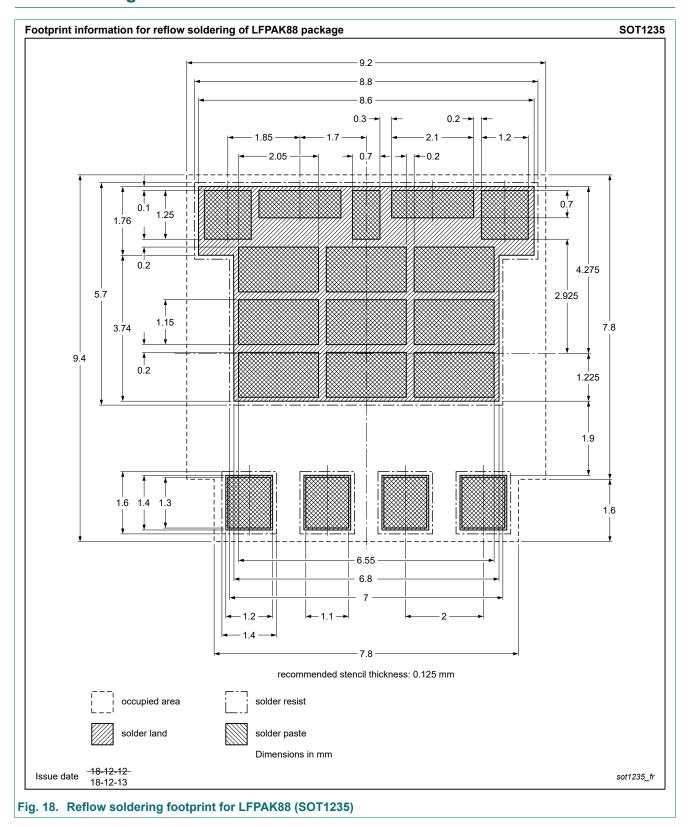


Fig. 17. Package outline LFPAK88 (SOT1235)

# 12. Soldering



### 13. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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